

Description

The RST0275 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in automotive applications and a wide variety of other applications.

General Features

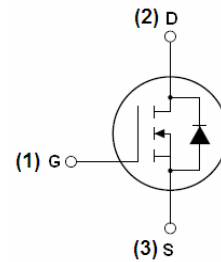
- $V_{DSS} = 200V, I_D = 75A$
 $R_{DS(ON)} < 20m\Omega @ V_{GS} = 10V$
- Good stability and uniformity with high E_{AS}
- Special process technology for high ESD capability
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Automotive applications
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔV_{DS} TESTED!



Schematic diagram



Marking and pin assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
RST0275	RST0275	TO-220-3L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DSS}	200	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	75	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D (100^\circ C)$	53	A
Pulsed Drain Current	I_{DM}	300	A
Maximum Power Dissipation	P_D	360	W
Derating factor		2.4	W/ $^\circ C$
Single pulse avalanche energy (Note 3)	E_{AS}	1512	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 1)	$R_{\theta JC}$	0.42	°C/W
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

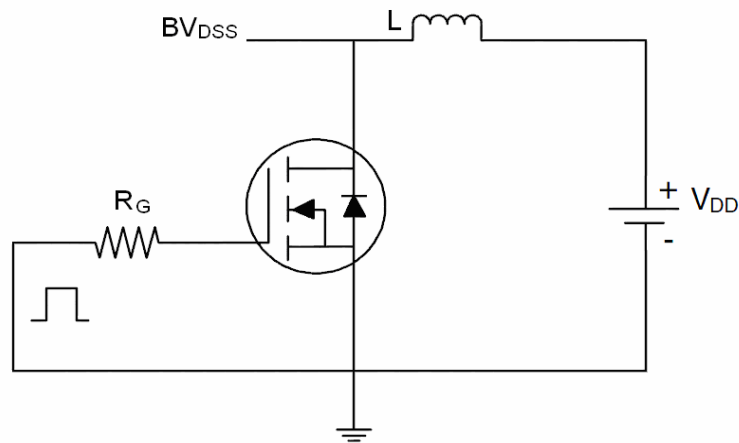
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	200	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =200V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±200	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.5	3.5	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	17.8	20	mΩ
Forward Transconductance	g _{FS}	V _{DS} =50V, I _D =40A		79	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	6990	-	PF
Output Capacitance	C _{oss}		-	950	-	PF
Reverse Transfer Capacitance	C _{rss}		-	700	-	PF
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =100V, I _D =40A, V _{GS} =10V, R _G =2.7Ω	-	17	-	nS
Turn-on Rise Time	t _r		-	18	-	nS
Turn-Off Delay Time	t _{d(off)}		-	56	-	nS
Turn-Off Fall Time	t _f		-	22	-	nS
Total Gate Charge	Q _g	ID=40A, VDD=100V, VGS=10V	-	140	-	nC
Gate-Source Charge	Q _{gs}		-	40	-	nC
Gate-Drain Charge	Q _{gd}		-	45	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =75A	-	-	1.2	V
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 40A	-	136	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/μs ^(Note2)	-	458	-	nC

Notes:

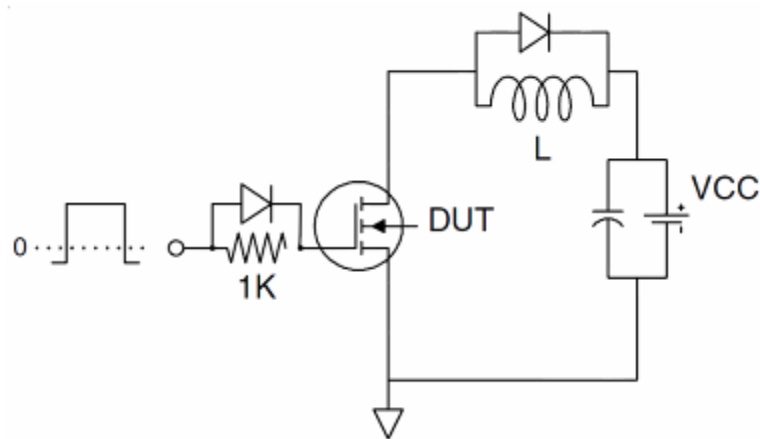
1. Surface Mounted on FR4 Board, $t \leq 10$ sec.
2. Pulse Test: Pulse Width $\leq 400\mu s$, Duty Cycle $\leq 2\%$.
3. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=1mH, R_G=25\Omega, I_{AS}=55A$
4. $I_{SD} \leq 125A, di/dt \leq 260A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^{\circ}\text{C}$

Test Circuit

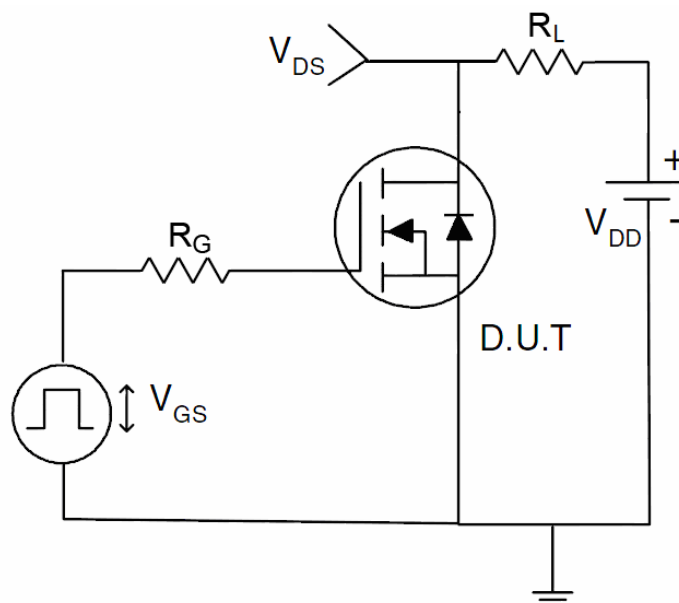
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

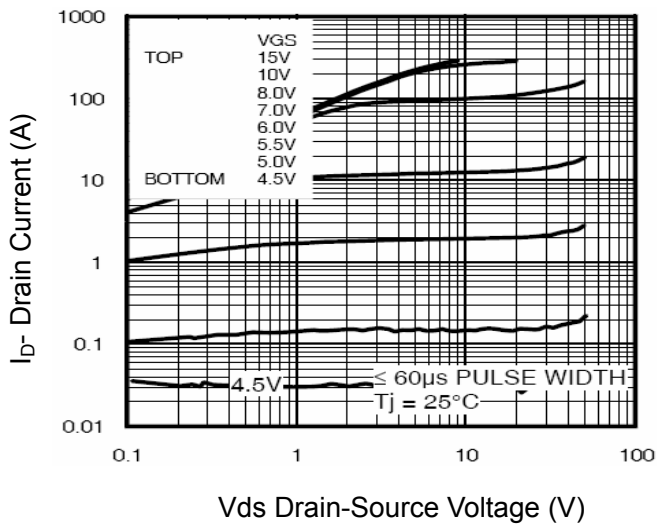


Figure 1 Output Characteristics

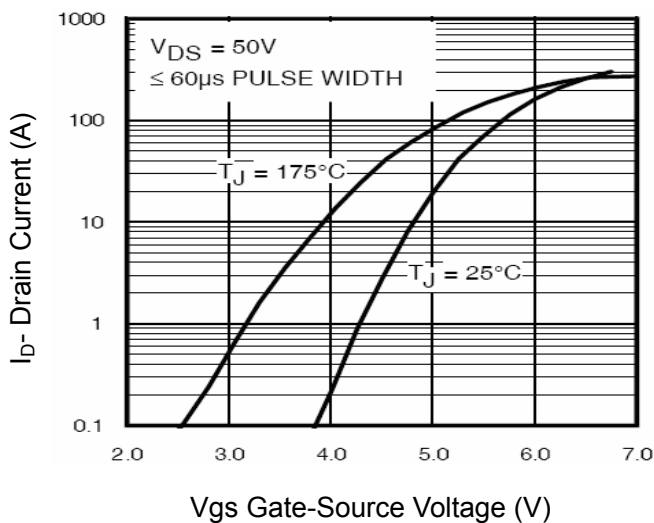


Figure 2 Transfer Characteristics

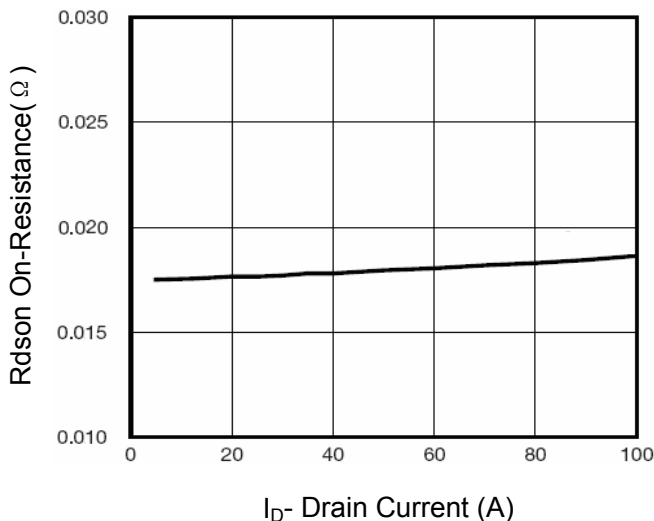


Figure 3 $R_{DS(on)}$ - Drain Current

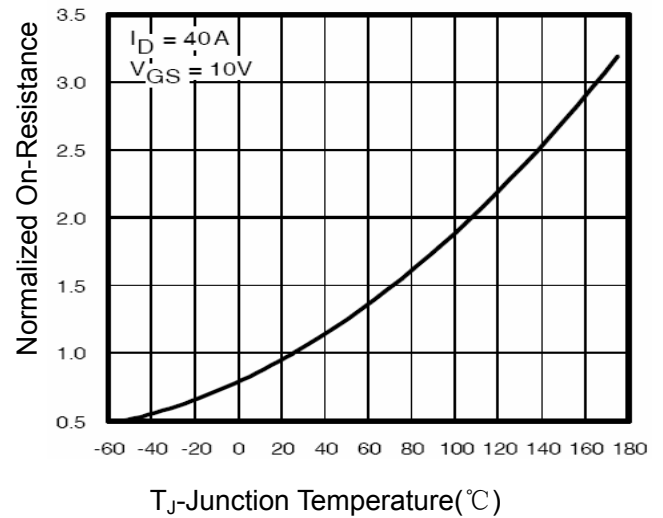


Figure 4 $R_{DS(on)}$ -Junction Temperature

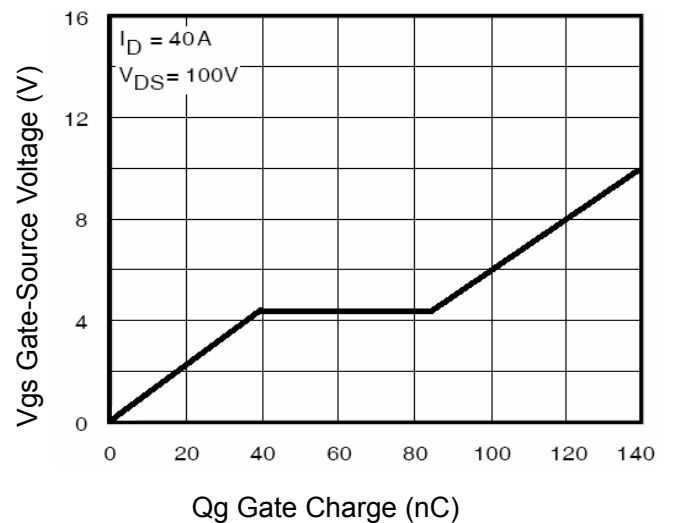


Figure 5 Gate Charge

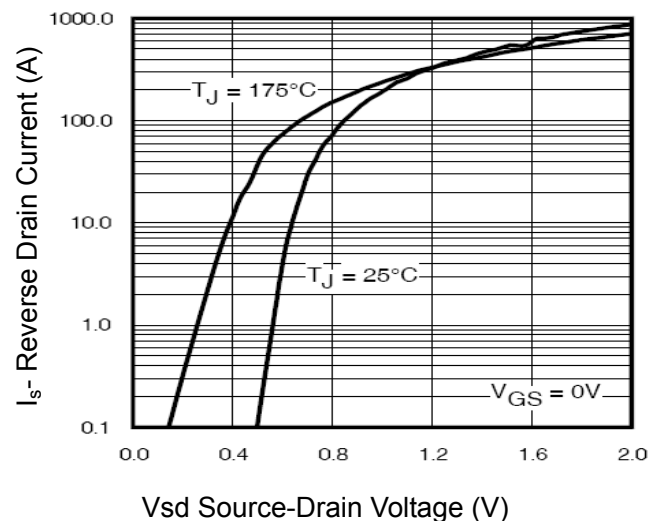
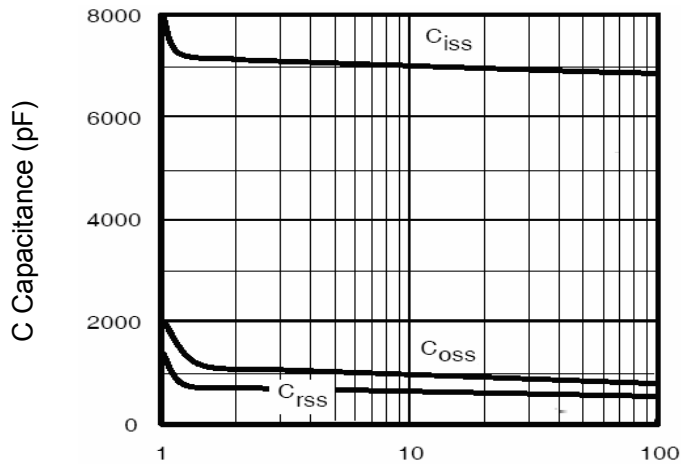
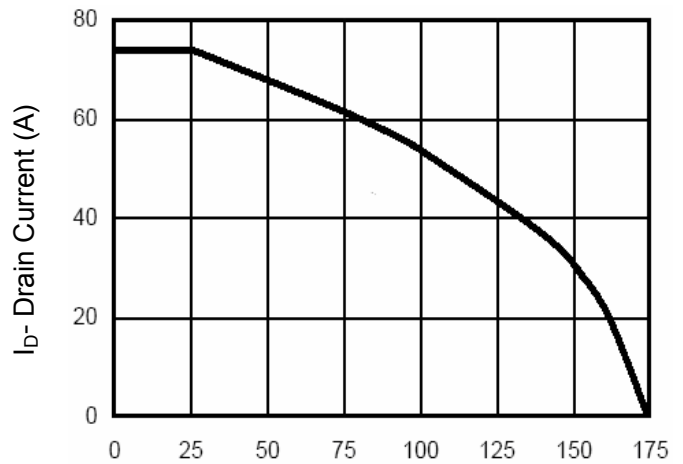


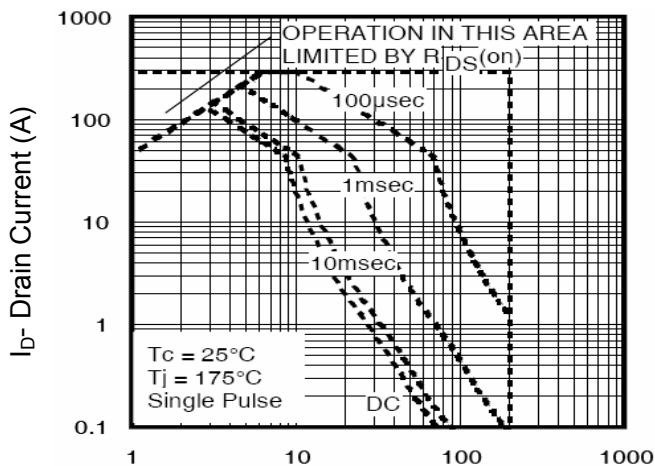
Figure 6 Source- Drain Diode Forward



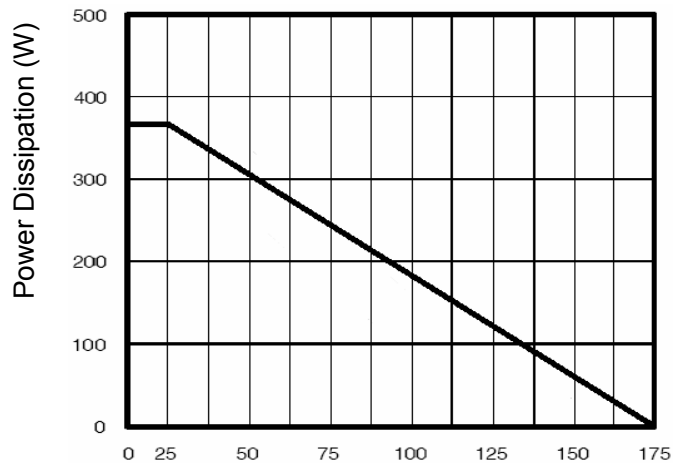
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



T_J-Junction Temperature(°C)
Figure 9 ID Current Derating vs Junction Temperature



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



T_J-Junction Temperature(°C)
Figure 10 Power De-rating

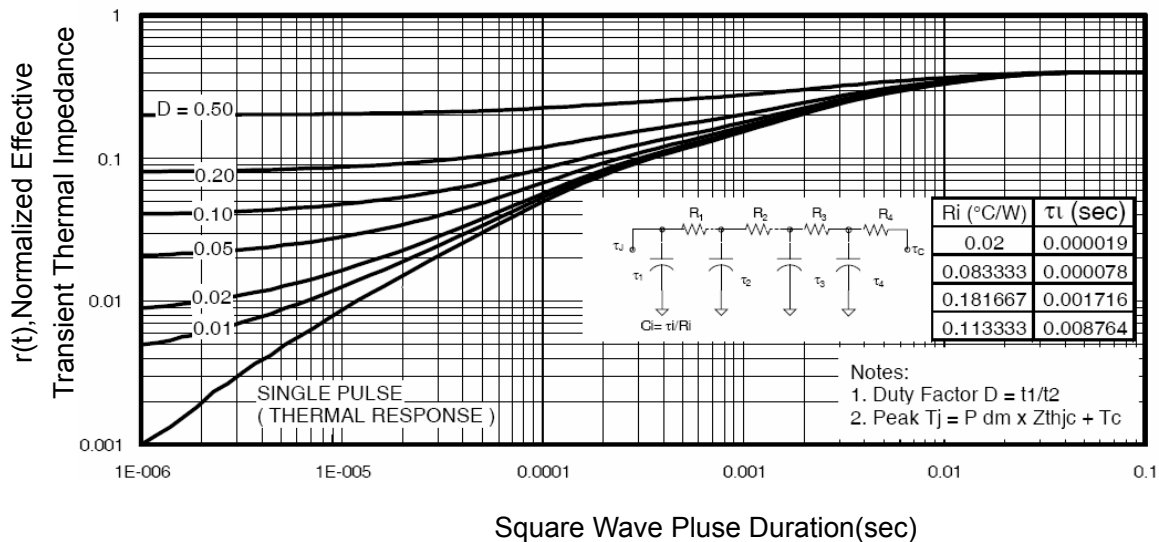
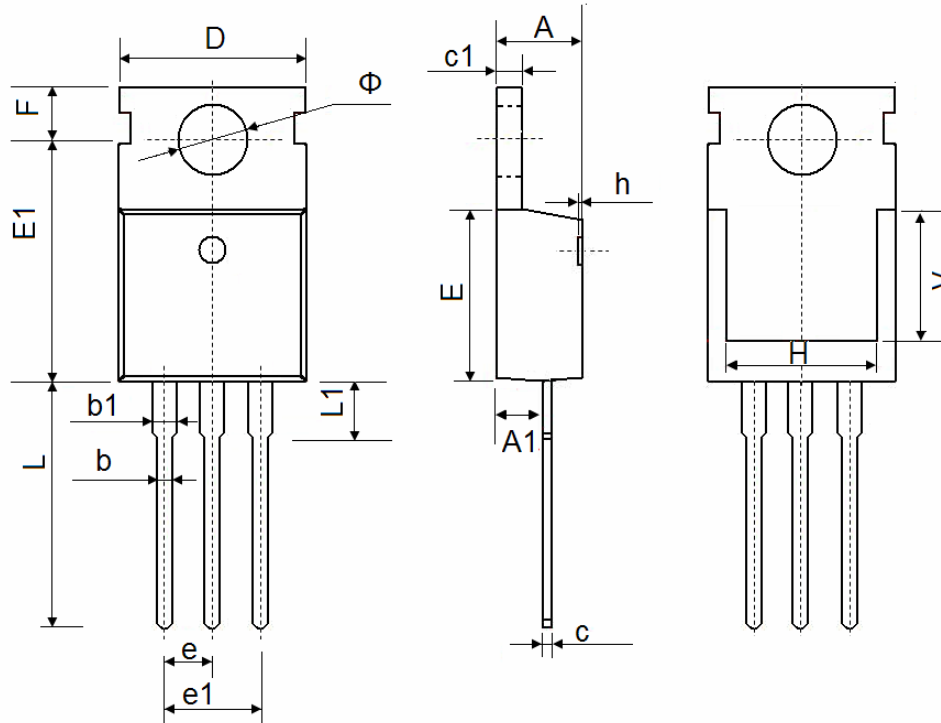


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150